





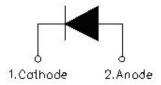
SDURK30F60 ULTRAFAST RECTIFIER



Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- · Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- Terminals finish: 100% Pure Tin
- This is a Pb free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings(T_C =25°C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	600	V
Average Rectified Forward Current	I _{F (AV)}	Tc=70°C, In DC	30	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	150	А

- China Germany Korea Singapore United States
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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 15A, Pulse, T _J = 25°C	1.38	-	V
		@ 30A, Pulse, T _J = 25°C	1.66	2.20	V
	V _{F1}	@ 15A, Pulse, T _J = 125°C	1.20	-	V
		@ 30A, Pulse, T _J = 125°C	1.48	2.00	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J =25°C	0.009	10	uA
	I _{R2}	@V _R = rated V _R , T _J =125°C	0.006	1	mA
Reverse Recovery Time	t _{rr}	I_F =500mA, I_R =1A,and I_m =250mA, T_J = 25°C	29	40	ns
Reverse Recovery Time	t _{rr}	L = 20A d:F/dt = 240A/::=	104	-	ns
Reverse Recovery Charge	Qrr	│ I _F = 30A, diF/dt = -210A/μs │ V _R = 380V. T _J = 25°C	285	-	nC
Reverse Recovery Current	I _{RRM}	VR = 380V, 1J = 23 C	5.2	-	Α
Reverse Recovery Time	t _{rr}	L = 20A diF/dt = 210A/up	144	-	ns
Reverse Recovery Charge	Qrr	│ I _F = 30A, diF/dt = -210A/μs │ V _R = 380V. T _J = 125°C	828	_	nC
Reverse Recovery Current	I _{RRM}	VR - 300V, 1J - 123 C	8.4	-	Α

 $^{^{\}star}$ Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

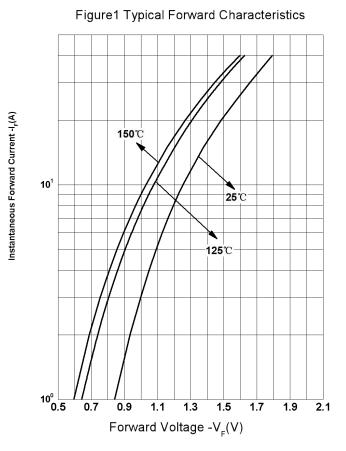
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	3.5	°C/W
Approximate Weight	wt	-	1.6	g
Case Style	ITO-220AC-2L			

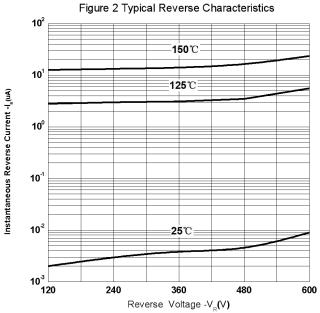


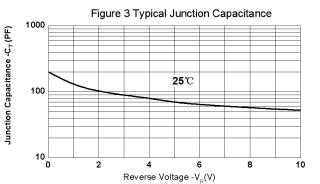




Ratings and Characteristics Curves







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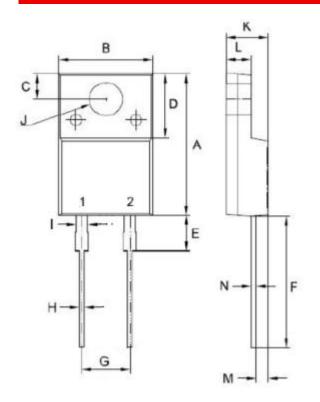
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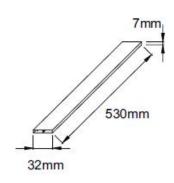


Mechanical Dimensions ITO-220AC-2L

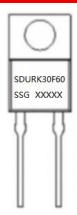


2,4,5,2,	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	14.50	15.30	16.00		
В	9.50	10.00	10.50		
С	2.50	3.00	3.5		
D	6.30	6.80	7.30		
E	3.10	3.70	4.30		
F	13.00	13.5	14.00		
G	4.90	5.10	5.30		
Н	0.30	0.60	0.90		
I	0.90	1.2	1.50		
J	3.20	3.50	3.80		
K	4.24	4.54	4.84		
L	2.30	2.61	2.92		
М	1.09	1.29	1.49		
N	0.42 0.53		0.63		

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

SDUR = Device Type
K = Package type
30 = Forward Current (30A)
F = F
60 = Reverse Voltage (600V)
SSG = SSG

YY = Year WW = Week L = Lot Number

Ordering Information:

Device	Package	Shipping
SDURK30F60	ITO-220AC-2L(Pb-Free)	50pcs / tube

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SDURK30F60



Technical Data Data Sheet N2753, Rev. -





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